TOSHIBA 1SV262

TOSHIBA VARIABLE CAPACITANCE DIODE SILICON EPITAXIAL PLANAR TYPE

1 S V 2 6 2

CATV TUNING

High Capacitance Ratio : C2V/C25V = 12.5 (Typ.)

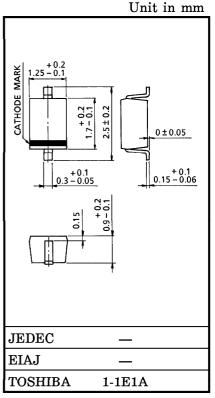
Low Series Resistance : $rs = 0.6\Omega$ (Typ.)

Excellent C-V Characteristics, and Small Tracking Error.

Small Package

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Reverse Voltage	$v_{ m R}$	34	V
Peak Reverse Voltage	$v_{ m RM}$	$36 (R_L = 10 k \Omega)$	V
Junction Temperature	$\mathrm{T_{j}}$	125	$^{\circ}\mathrm{C}$
Storage Temperature Range	$\mathrm{T_{stg}}$	-55~125	$^{\circ}\mathrm{C}$



Weight: 0.004g

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Reverse Voltage	$V_{ m R}$	$I_R = 1 \mu A$	34	_	_	V
Reverse Current	I_{R}	$V_R = 32V$	_	_	10	nA
Capacitance	C2V	$V_R = 2V, f = 1MHz$	33	35.5	38	pF
Capacitance	C25V	V_R =25 V , f=1 MHz	2.6	2.85	3.0	pF
Capacitance Ratio	C2V / C25V	-	12.0	12.5	_	_
Capacitance Ratio	C25V / C28V	_	1.03	_	_	_
Series Resistance	r_{S}	$V_R=5V, f=470MHz$	_	0.6	0.8	Ω

(Note 1) : Available in matched group for capacitance to 2.0% MARKING

$$\frac{C \text{ (Max.)} - C \text{ (Min.)}}{C \text{ (Min.)}} \le 0.02 \text{ (VR} = 2 \sim 25 \text{V)}$$

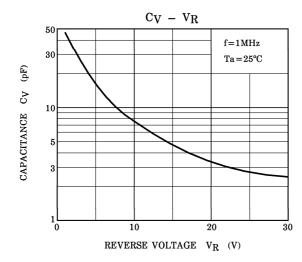


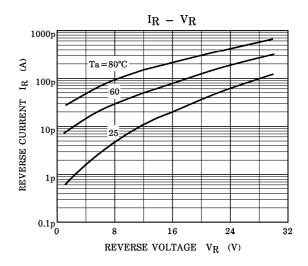
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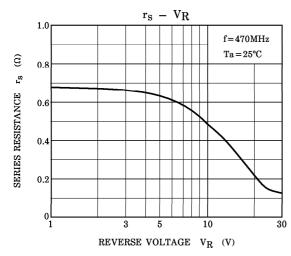
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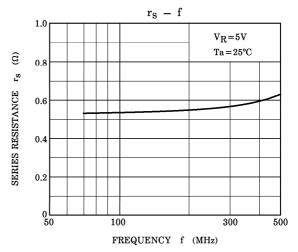
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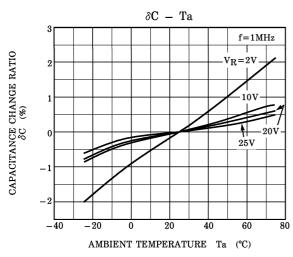
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SPICE PARAMETER

SPICE MODEL : BERKLEY SPICE.2G.6 DIODE MODEL

DATA FORMAT : MODEL FORMAT

SPICE SYMBOL : $I_{S}(A)$, $R_{S}(\Omega)$, N(-), $CJ_{O}(F)$, $V_{J}(V)$, M(-), $B_{V}(V)$, $I_{BV}(A)$

FREQUENCY RANGE : $f = 0.1 \sim 3 \text{ GHz}$

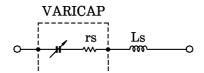
REVERSE VOLTAGE RANGE : $V_R = 2 \sim 25 \text{ V}$

: $Ta = 27^{\circ}C$ AMBIENT TEMPERATURE

PARAMETER

Ls

= 1.00E - 09



(Note 1): These parameters from Ig to M mean die characteristic. Actually device has lead inductance so Ls is necessary for simulation. And please use default value except above parameters.

(Note 2): RS shows the value at the condition of $V_R = 5\,V$ and $f = 470\,MHz$. If another value is needed, please refer to RS - VR curve in this data sheets.